

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): An n-type ohmic electrode for use with an n-type Group III nitride semiconductor, which is provided to contact with the surface of an n-type Group III nitride semiconductor layer, wherein the n-type ohmic electrode layer is made of an alloy of aluminum (atomic symbol: Al) and lanthanum (atomic symbol: La) or comprises lanthanum, and wherein the lanthanum content in the n-type ohmic electrode layer is 10 mass% or more on the surface contacting with the n-type Group III nitride semiconductor layer.

2. (canceled).

3. (currently amended): The n-type ohmic electrode according to ~~claim 2~~^{claim 1}, wherein the lanthanum content in the n-type ohmic electrode layer is less than 10 mass% in the region 30 nm or more distant from the junction interface with the n-type Group III nitride semiconductor layer.

4. (original): The n-type ohmic electrode according to claim 3, wherein the surface of the n-type ohmic electrode layer opposite the surface contacting with the n-type Group III nitride semiconductor layer is made of aluminum.

5. (currently amended): A semiconductor light-emitting device fabricated by providing an ohmic contact electrode on a stacked structure body in which an n-type Group III nitride semiconductor layer and a p-type compound semiconductor layer are provided on one surface of a crystalline substrate and a light-emitting layer is interposed between the n-type and p-type compound semiconductor layers, wherein the n-type ohmic electrode provided to contact

with the n-type Group III nitride semiconductor layer is made of a lanthanum-aluminum alloy layer or a lanthanum layer, the n-type ohmic electrode comprises a lanthanum-aluminum alloy layer has a lanthanum content of 10 mass% or more at the junction interface with the n-type Group III nitride semiconductor layer and has a lanthanum content of less than 10 mass% in the region 30 nm or more distant from the junction interface.

6. (original): The semiconductor light-emitting device according to claim 5, wherein the n-type ohmic electrode comprises a lanthanum-aluminum alloy layer or a lanthanum layer in the side contacting with the n-type Group III nitride semiconductor layer and comprises an aluminum layer in the opposite side.

7. (canceled).

8. (withdrawn - currently amended): A method for forming an n-type ohmic electrode, comprising for use with an n-type Group III nitride semiconductor, which is provided to contact with the surface of an n-type Group III nitride semiconductor layer, wherein the n-type ohmic electrode layer is made of an alloy of aluminum (atomic symbol: Al) and lanthanum (atomic symbol: La) or comprises lanthanum, and wherein the lanthanum content in the n-type ohmic electrode layer is 10 mass% or more on the surface contacting with the n-type Group III nitride semiconductor layer, which method comprises forming a lanthanum-aluminum alloy layer constituting the n-type ohmic electrode, by using a lanthanum-dialuminum alloy (compositional formula: LaAl₂) as a raw material.

9. (original): The method for forming an n-type ohmic electrode according to claim 8, wherein the lanthanum-aluminum alloy layer is provided to join it to the surface of an n-type Group III nitride semiconductor layer while setting the n-type Group III nitride semiconductor layer at 300°C or less, thereby forming an n-type ohmic electrode from a lanthanum-aluminum

alloy layer having a lanthanum content of 10 mass% or more at the junction interface and having a lanthanum content of less than 10 mass% in the region 30 nm or more distant from the junction interface.

10. (withdrawn - currently amended): A method for producing a semiconductor light-emitting device, comprising fabricated by providing an ohmic contact electrode on a stacked structure body in which an n-type Group III nitride semiconductor layer and a p-type compound semiconductor layer are provided on one surface of a crystalline substrate and a light-emitting layer is interposed between the n-type and p-type compound semiconductor layers, wherein the n-type ohmic electrode provided to contact with the n-type Group III nitride semiconductor layer is made of a lanthanum-aluminum alloy layer or a lanthanum layer, the n-type ohmic electrode comprises a lanthanum-aluminum alloy layer has a lanthanum content of 10 mass% or more at the junction interface with the n-type Group III nitride semiconductor layer and has a lanthanum content of less than 10 mass% in the region 30 nm or more distant from the junction interface, which method comprises providing an ohmic contact electrode on a stacked structure body in which an n-type Group III nitride semiconductor layer and a p-type compound semiconductor layer are provided on one surface of a crystalline substrate and a light-emitting layer is interposed between the n-type and p-type compound semiconductor layers, wherein the lanthanum-aluminum alloy layer constituting an n-type ohmic electrode which contacts with the n-type Group III nitride semiconductor layer is formed by using a lanthanum-dialuminum alloy (compositional formula: LaAl₂) as a raw material.

11. (original): The method for producing a semiconductor light-emitting device according to claim 10, wherein the lanthanum-aluminum alloy layer is provided to join it to the surface of the n-type Group III nitride semiconductor layer while setting the n-type Group III

nitride semiconductor layer at 300°C or less, thereby forming an n-type ohmic electrode from a lanthanum-aluminum alloy layer having a lanthanum content of 10 mass% or more at the junction interface and having a lanthanum content of less than 10 mass% in the region 30 nm or more distant from the junction interface.